PROCESSING OF ZrB₂-ZrC-Zr_xSi_y CERAMIC BY REACTIVE METAL

PENETRATION

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ABSTRACT

The processing of ZrB $_2$ -ZrC-Zr_xSi_v composite by reactive metal penetration was investigated as a successor to the ZrB $\qquad \qquad$ 2-SiC composites for hypersonic vehicles application, which cannot be used for extended time at temp eratures greater than 1600C due to formation of SiO and CO gases. Zirconium (Zr), zirconium disilicide $(ZrSi₂)$, and boron carbide (B₄C) were reacted in graphite crucibles for 60, 120, 180, and 240 minutes. Microscopy and x -ray diffraction (XRD) deduced the formation of a heterogeneous microstructure of ZrB $_2$ -ZrC-Zr_xSi_v precipitates surrounded by a solidified Zr-Si melt. Unreacte d boron carbide was observed in samples held at 1860 °C for 60 minutes and 120 minutes, so thermodynamic equilibrium was not achieved . The reaction for the composite formation is as follows:

 $Zr+B_4C+ZrSi_2 \longrightarrow ZrB_2+ZrC+Zr_xSi_v$

The most consistent microstructures were seen on the samples heated for 180 mi nutes and 240 minutes, in which the free B $_{4}C$ completely decomposed to zirconium boride and carbide. Also, because of the closeness of the initial compositions of Zr and Si (12 wt% and 14 wt%) on the Zr-Si phase diagram, there was not much difference in the final phases obtained in both compositions.

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Chapter 1: INTRODUCTION

1.1: Overview of Ultra-High Temperature Ceramics

The wing leading edge and nose caps of the hypersonic vehicles are subject ed to temperatures greater than 2000° C during their reentry and sustain severe conditions caused by vaporization, erosion and oxidation. In addition to chemical reactivity, the durability of materials to ultrahigh temperatures (>1600°C) causes severe mechanical interaction resulting from thermal shock for ceramic mat erials as they cycle from room temperature to the extreme temperatures. The composites must then sustain a synergistic effect contributed from the chemical and mechanical interactions at ultrahigh temperatures exposure, requiring selection of the optimal material system.

The carbides and borides of the transition metals (e.g., ZrC, HfC, ZrB $_2$ and HfB $_2$) have been suggested as materials for ultrahigh temperature ceramics [Opeka-2004, Bronson-1992], because of their exceptionally high melting temperatures of greater than 3000°C. The other important distinctive qualities are solid-state stability, good thermomechanical properties, and high mechanical properties, values as shown in table 1.1. However, a scale must protect the foregoing carbides and borides, which readily react with oxygen. Various researchers [Hinze-1975, Karlsdottir-2007, Fahrenholtz - 2007, and Monteverde-2007] determined through their meticulous study that the ZrB $_{2}$ -SiC system is protected from oxidation because an adherent silicate scale forms and decreases significantly the diffusion of oxygen into the substrate . However, the formation of SiO and CO limits the operational temperature of SiC because the CO forms along the SiC/ $SiO₂$ interface as well as SiO (g) creates a bubbling action at

temperatures greater than 1600 -1700°C [Levine-2002, Bronson -2008,]. Hence, a silicide must be found without the formation of gaseous products though still with the protective properties of a silicate layer, which lowers the oxygen diffusion.

 $3Zr+B_4C \longrightarrow 2ZrB_2+ZrC$ (1.1) An additional drawback of ultrahigh temperature materials is their processing because the systems require ultrahigh temperatures, controlled porosity and significantly low impurities. For example, ZrB $_2$ and ZrC have melting points of 3244 °C [Okamoto-1993] and 3427°C [Okamoto-1996], respectively, but SiO $_2$ impurities coalescing in the grain boundaries would lower the yield strength. Johnson et al. [6] developed a technique of reacting liquid Zr with a packed bed of B_4C , the process called reactive metal penetration. As the Zr penetrates the packed bed, the following reaction ensues exothermically with the Gibbs free energy of formation at 1855 °C, $\Delta G = -673$ kJ:

An additional contribution would be to use a Zr -Si melt instead of Zr melt to create a boride/carbide precipitates emb edded in a Zr -Si alloy matrix. Upon oxidation, the Si would react to form a silicated layer.

1.2: Research Objective

The research investigates the processing of a ceramic composite consisting of ZrB_2 , ZrC , Zr_XSi_V precipitates within a metal matrix of Zr -Si alloy. The objective of the research was to determine the extent of the silicide precipitation as the Zr -Si liquid penetrates the B4C packed bed. The original Zr-Si liquid corresponded to the Zr-12 wt% Si, which lies within the Zr_3S i-ZrSi two-phase region and $Zr-16$ wt% Si, which lies within the $Zr_2Si-Zr_3Si_2$ region of the Zr-Si phase diagram. The Zr_xSi_v would ultimately f orm a

protective $SiO₂$ and ZrO₂ scales to provide oxidation resistance to the composite. The liquid $SiO₂$ embedded in the ZrO₂ scales fills up the cracks resulting in stress reduction. The study investigated the processing $ZrB_2-ZrC-Zr_xSi_y$ composite by reactive metal penetration and its dependence on time.

$$
\lim_{t\to 0}\lim_{t\to 0}\frac{1}{t}
$$

Chapter 2: LITERATURE REVIEW

2.1: Processing of Ultra-High Temperature Ceramics

 There are several methods of processing ultra-high temperature ceramics (UHTC) though reactive metal penetration is an economical and uncomplicated technique of creating interconnecting precipitates in a metal/ceramic composite, without hot pressing . F or considering systems suitable for reactive metal penetration, the thermodynamic reactions and thermodynamic compatibility of phases must be determined [Fahrenholtz-2006]. The reactions should be thermodynamically favorable which refers to the Gibb's free energy of reaction, as shown in figure 2.1. The Gibbs free energy of ZrC is considerably less than B4C and the liquid would displace the boron via the reaction shown in equation 1.1. The phase equilibria must then be checked with phase diagrams, if available.

2.1.1: Reactive Metal Penetration

Tomsia et al. [5] and Johnson et al. [6] have used reactive metal penetration to form a composite by capitalizing on interfacial reaction between a metal and ceramic. Tomsia et al. [5] reacted molten aluminum with mullite to form Al_2O_3 with Al-Si alloy. The liquid aluminum penetrated the silicate preform dissolving $SiO₂$ and forming $Al₂O₃$ at the reaction layer. The process continues with oxygen diffusing through the initial Al $_{2}O_{3}$ product and reacting with molten aluminum forming more $Al \qquad 2O_3$. The dissolved Si moves away from the reaction zone forming Al-Si alloy.

 $3(AI_2O_3.2SiO_2) + (8+x)Al \longrightarrow 13Al_2O_3 + Al_xSi_y + (6-y)Si$ (2.1)

 Similarly, Johnson et al. [6] reported that molten zirconium infiltrated through the open porosity of B₄C reacting to f orm simultaneously precipitates of ZrB₂ and ZrC. The dissolution of B $_4$ C re sults in a thin boron -rich zirconium alloy. The boron-rich zirconium alloy pulls down the previously formed ZrB 2 -ZrC layer by transportation phenomena and at the same time, reacting to leave behind a $ZrB₂-ZrC-Zr$ composite. Liquid metal can infuse into a ceramic preform by creating a pressure difference between the outer wall and inner core as aluminum or zirconium penetrating the ceramic preforms of mullite (3Al $_2O_3.2SiO_2$), SiO_2 or B₄C [Bronson-1997]. For cera mics with low open porosity, Odegard and Bronson considered capillary motion driven by surface tension instead of pressure difference for transporting the liquid metal with the reaction shown in equation 1.1.

For the ZrB $_2$ -ZrC-Zr_xSi_v system, with the addition of ZrSi $_2$ to the initial constituents, the Zr serves as a carrier for Si when liquid Zr -Si penetrates into a preform. Zirconium silicides form upon cooling and their composition depends on the initial zirconium and zirc onium disilicides. The reaction occurs very fast with linear kinetics with a rate constant between 1.6×10^{-2} 12 and 3.9×10 12 cm²/s [Tomsia-1999, Johnson-1991]. Initially, the rate -determining step will be the interfacial reaction between Zr-Si melt and boron c arbide. Once the reaction initiates, the boron carbide – liquid Zr-Si reaction will be faster tha n the diffusion of Si, B and C [Johnson-1991, Lu-1999, Tomsia-1999, Fahrenholtz-2006,].

$$
(3+x)Zr + B_4C + yZrSi_2 \longrightarrow 2ZrB_2 + ZrC + Zr_xSi_{2y}
$$
 (2.3)

2.2: Phase Diagrams

2.2.1: Zr-Si Phase Diagram

The Zr-Si phase diagram gives the phase equilibria with a maximum melting at 2250 \degree C for Zr $_5$ Si₄ compound, as shown in figure 2.2. The melting temperatures of Si and Zr are 1414 \degree C and 1855 \degree C respectively. Eutectic reactions occur on either side of binary - at 1370 °C in the Si-rich region (10 at% Zr) and at 1570 °C in the Zr-rich region (91.2 at $%$ Zr). The maximum solubility of Si in Zr is less than 1 at $%$ Si (due to the relatively large size of Zr atom) forming Zr (body centered cubic, BCC) and Zr (hexagonal close packed, HCP), but Zr is not soluble in Si . The Zr -Si system has the following intermetallic compounds: $ZrSi_2$, $ZrSi$ and Zr_5Si_4 and Zr_5Si_4 , Zr_3Si_2 , Zr_5Si_3 , Zr_2 Si and Zr_3 Si. The $ZrSi_2$ (33 at% Zr) phase initially forms at 1620 °C with a peritectic transformation of liquid and ZrSi. Similarly, ZrSi forms from the peritectic reaction of liquid and Zr $_5Si_4$ at 2210 °C though ZrSi structure changes at 1460 °C. Polymorphic transformations also occur at 1860 °C for Zr_5Si_4 and Zr_3Si_2 . The Zr_5Si_4 undergoes a congruent transformation at 2210 °C. The peritectic formation of Zr $_3Si_2$ (60 at% Zr) occurs at 2215 °C. The Zr_5Si_3 (62.5 at% Zr) also forms peritectically, but transforms with a eutectoid reaction at 1745 °C forming Zr_2Si and Zr_3Si_2 when cooled slowly. The Zr_5Si_3 is thermodynamically unstable at temperatures less than 1745 \degree C as indicated by the Zr-Si phase diagram. The incongruent reactions of Zr_2Si and Zr_3Si occur at 1925°C and 1650° C respectively.

Figure 2.1: Ellingham Diagram for Carbides [Outotec].

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2.2.2: B-C-Zr Phase Diagram

Isothermal sections of Zr-B-C system at temperatures, 1800 \degree C and 2400 \degree C are shown in figures 2.3 and 2.4. For the isothermal section at 1800° C, we observe four binary compounds, ZrB $_{2}$, ZrC, B $_{4}$ C, and ZrB $_{12}$; and the three -phase field, $ZrB_2+ZrC+LIQUID$ forms. The phase diagram shows no other liquid present apart from the unreacted molten zirconium. The three-phase field $(ZrB₂+ZrC+LIQUID)$ is a product of molten Zr reacting with B_4C . Phase layers such as $ZrC+B_4C$ and $ZrC+B_4C+C$ are also present at 1800 \degree C. At 2400 \degree C, boron-rich liquid exists due to the peritectic melting of ZrB_{12} at 2030 °C and eutectic reaction between ZrB_2 , B_4C , and C at 2165 °C. The Zr-rich liquid region grows larger at 2400 \degree C due to the d ecomposition of some of the ZrB2+ZrC+LIQUID phase.

2.2.3: Zr-B4C-ZrSi2 Phase Diagram

The pseudo-ternary system at 1860 \degree C shown in figures 2.5 contains three zirconium silicides, ZrSi, Zr₂Si and Zr₅Si₃; boride, ZrB₂; and carbide, ZrC. The FactSage database, which generated the phase diagram, does not consider the other silicide intermetallics from the Zr -Si phase diagram such as Zr_5Si_4 , Zr_3Si_2 and Zr_3Si . Zr and $ZrSi₂$ melt to form Zr-Si liquid, which then reacts with B₄C leaving behind a composite of ZrB_2 , ZrC and Zr $_XSi_V$, given sufficient time. The stable phases ZrB $_2$ and ZrC are in equilibrium with ZrSi and Zr $_5$ Si₃ between 30 at% ZrSi₂ and 5 at% ZrSi₂. The compound $\rm SiB_{14}$ is formed by the reaction between B₄C and SiB₆.

Figure 2.3: B-C-Zr Ternary Phase Diagram at 1800°C [Outotec].

Figure 2.4: B-C-Zr Ternary Phase Diagram at 2400°C [Outotec].

Figure 2.5: Zr-B4C-ZrSi2 Pseudo-Ternary Phase Diagram at 1860°C [FactSage].

2.3: Oxidation of ultra-high temperature ceramic

 Transition Metal (Zr, Hf, Ti and Ta) diborides and carbides are more suitable for use as ultra -high temperature ceramics (UHTC) because of their oxidation resistance by forming scales, there by, reducing oxygen ingress [Opeka-2004, Fahrenholtz-2007]. The oxidation resistance of borides and carbides can be increased by the addition of Si, which form a protective SiO $_2$ layer [Hinze-1975]. Researchers have reported the formation of multi -layer oxide scale upon oxidat ion of ZrB $_2$ -SiC composite at temperatures greater than 1500 \degree C [Hinze-1975, Karlsdottir -2007, Fahrenholtz-2007, Monteverde-2007]. Up to 1200 °C, the liquid $SiO₂-B₂O₃$ protects the composite by preventing oxygen diffusion a nd preventing scale spallation. At temperatures greater than 1200° C, the boria vaporizes from the outer borosilicate scale and completely at around 1500°C leaving behind an outer amorphous silica-rich scale with $ZrO₂$ precipitates covering a zirconia-rich scale with $SiO₂$ precipitates. This layered oxide scales are capable of extremely high temperature oxidation resistance due to the viscosity and wettability of SiO₂ glass layer. The diffusion of oxygen through the liquid $SiO₂$ layer is the rate-determining step and shows parabolic oxide scale growth rate. A simulated ZrO_2-SiO_2 scale on a $ZrB_2-ZrC-Zr$ composite is shown in figure 2.6.

2.3.1 Zr-Si-O Phase Diagram

From the Zr-Si-O ternary phase diagram shown in figure 2.7 , the equilibrium phases , which must be present at 1680 °C, are $ZrO₂$ (solid), SiO₂ (liquid) and ZrSiO ₄. A discrepancy exists in this phase diagram as $ZrSiO₄$ is shown to be present even though the pseudo-binary ZrO_2-SiO_2 phase diagram (figure 2.8) suggests dissociation of $ZrSiO_4$

the pseudo-binary ZrO_2-SiO_2 phase diagram (figure 2.8) suggests dissociation of $ZrSiO_4$ at 1673 °C. The ZrO₂-ZrSi₂ tie line prevents other silicides from equilibrating with SiO $_2$ and ZrSiO₄.

2.3.2 ZrO₂-SiO₂ Phase Diagram

The pseudo -binary phase diagram of ZrO $_{2}$ -SiO₂ in figure 2 . & h o w s compound Zircon (ZrSiO₄), which decomposes in solid state at 1673 °C into solids, ZrO₂ and $SiO₂$. The two solid phases, ZrO₂ and SiQ , co-exist represented by the horizontal tie lines between 1687°C and 1673°C and $SiO₂$ melting temperature is 1723°C. Eutectic reaction occurs on the SiO ₂-rich region at 1687 °C, but SiO $_2$ is not sol uble in ZrO $_2$. The melting temperature of ZrO $_2$ is 26 \mathcal{L} and exists as monoclinic - ZrO $_2$ at room temperature with transformation to tetragonal - $ZrO₂$ at 1205°C and the tetragonal - $ZrO₂$ to cubic fluorite - $ZrO₂$ transformation at 2370 °C. There is a 9% volume increase when tetragonal - $ZrO₂$ transforms to monoclinic - $ZrO₂$. The liquidus line exists over the entire region with a miscibility gap between 2250°C and 2430°C indicated by L1 + L2.

Figure 2.7: Zr-Si-O Ternary Phase Diagram at 1680°C [Sorrell-1986].

Figure 2.8: ZrO2-SiO² Pseudo-Binary Phase Diagram [Kaiser-2008].

Chapter 3: RESEARCH METHODOLOGY

3.1: Sample Preparation

 B_4C powder (99+%, < 10 micron) and ZrSi₂ (99.5%, -325 mesh) supplied by Alfa Aesar was packed into a graphite crucible (0.5" OD, 1mm thick and 0.6" length) acquired from LECO. Zr slugs (99.5%, 3.175 mm diameter and 3.175 mm length), also obtained from Alfa Aesar, and was then placed on top of the $ZrSi₂$ powder. Graphite covers were used at the top of the graphite crucibles to push back the levitating Zr -Si melt. Two different compositions of ZrSi₂ were used, 0.57 g and 0.8 g, with the weights of B₄C (0.25 g) and Zr (1.5 g) kept constant. The 0.57 g sample corresponds to Zr -12wt%Si and 0.8 g sample corresponds to Zr-16wt%Si on the Zr-Si phase diagram. The sample setup is shown is figure 3.1.

Figure 3.1: Sample Setup.

The samples were then placed in a grap hite enclosure (Figures 3.3 and 3.4) machined from a graphite rod (2×17) diameter \times 17" length) acquired from American Graphite Corporation. Figure 3.2 shows the gra phite enclosure insulated by zirconia

grog (-8/+20 mesh) sourced from Zircoa. A zirconia crucible sufficiently shielded the graphite enclosure from the high magnetic fields generated by the induction furnace . GM Associates supplied the quartz reaction tube and CoorsTek, Inc supplied the zirconia crucible stabilized with Y_2O_3 (35 mm diameter \times 64 mm length). Pure aluminum wire (99.999%, 0.81mm diameter) procured from Alfa Aesar was rolled around the bottom part of the graphite enclosure, which oxidized to form a seal, thereby creating an inert atmosphere inside the graphite crucible . Titanium slugs and aluminum slugs were placed in the Al -Ti melt pit, as shown in figure 3.4, was used for the purpose of removing any residual oxygen left inside the graphite enclosure. The titanium slugs (99.5%, 3.175 mm diam eter and 3.175 mm length) and aluminum slugs (99.5%, 3.175 mm diameter and 3.175 mm length) were sourced from Alfa Aesar.

3.2: Experimental Procedure

The ZrB $_{2}$ -ZrC-Zr_xSi_Y composite was processed in a n i nduction furnace with operating frequency of 4.5 MHz with temperature controlled by an Ircon Maxline CPU™ infrared pyrometer sighting on the graphite enclosure . The induction furnace was acquired from Thermal Technology Inc. The set temperature was little more than the melting temperature of Zr at 1860 \degree C, but due to the exothermic reactions, temperatures inside the graphite enclosure will be in the region of $2300\degree$ C – $2400\degree$ C [Johnson-1991]. Deoxidized helium gas was p assed through the entire setup, which is shown in figure 3.5. Helium gas was preferred over argon gas to avoid plasma formation . The purification of helium was achieved in 3 steps. First, h elium gas was passed through a column of magnesium perchlorate to remove moisture. Two subsequent steps of passing the He gas through tubes containing titanium sponge, obtained from Alfa Aesar,

column of magnesium perchlorate to remove moisture. Two subsequent steps of passing the He gas through tubes containing titanium sponge, obtained from Alfa Aesar, deoxidized the gas. The first tube with titanium sponge was mainta 700° and the second tube was maintained at 800°C bringing down the oxygen potential of helium gas to 10^{-60} atm before entering the reaction tube setup. The helium gas was vented out into a dibutylphilate bubble r. Diagrams of the reaction tube, reaction tube ca p, cooling jacket, lower bottom reaction tube cap, and cooling jacket cap are shown from figures $3.6 - 3.10$.

The experiments were successfully run by holding the induction furnace at 1860 °C for 60, 120, 180, and 240 minutes with the last reacting time giving sufficient time for the entire melt to equilibrate. The temperature ramp rate was 30 °C/minute from room temperature to 1000 °C and 8 °C/minute from 1000 °C to 1860 °C, which is the set temperature. At the end o f the experiment, rapid cooling was maintained to freeze the microstructure achieved at higher temperatures. Temperature calibration was achieved by placing platinum wire on the graphite enclosure, which could be seen through the sighting tube of the pyrom eter. When the platinum wire melted at its melting temperature of 1773 °C, the temperature was increased on the controller by 87 °C, the difference between the set temperature of 1860 °C and platinum melting temperature of 1773°C.

3.3: Microstructure Characterization

The processed samples were cut along its length using a Struers – Accutom 2

table saw equipped with a diamond cut -off wheel. The cross -sections were then mounted on epoxy resin supplied by Pace Technologies and prepared by grinding with 120, 240, 4 00, 600, 800, and 1000 grit paper and finished by polishing with 1μ m diamond paste. The polished samples were rinsed with water and methanol before drying them with a blower. The microstructures of the cross -sectioned samples were analyzed with scanning electron microscope (Hitachi), optical microscope (Reichter) and X-ray diffractometer (Bruker) \blacksquare T h A -ray diffractometer was operating with an accelerating voltage of 40 kV and a beam current of 40 mA for an angle 2θ of 10°-70°.

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Figure 3.3: Graphite Enclosure with Graphite Crucible Sample.

Figure 3.4: Cross-section of the Graphite Enclosure.

Figure 3.8: Quartz Reaction Tube.

Figure 3.7: Cooling Jacket.

Figure 3.9: Bottom Reaction Tube Cap.

Figure 3.10: Cooling Jacket Cap.

Chapter 4: RESULTS

In this chapter, X -ray diffraction patterns and micrographs of the e processed composites are described . The starting compositions of the samples were Zr -12wt%Si and Zr -16wt%Si with B $_4$ C constant at 0.25 g and they were heated at the set temperature of 1860 °C for 60, 120, 180, and 240 minutes. The formation of pellet-like composites was not possible due to the zirconium levitation caused by the electromagnetic field of the induction furnace. The electromagnetic field brought about mixing of the melt at different places inside the graphite crucible leaving behind a highly heterogeneous microstructure . Description of accurate interfacial reactions, which occurred during the process, is not feasible due to the melt solidifying at different places on the graphite crucible. All samples observed showed varying porosity and grain size with greater porosity for shorter duration of reaction time . The increased porosity for shorter reaction times is due to the incomplete reactions between the free B₄C and the Zr-Si melt. An example of a levitating composite is shown in figure 4.1. Visual inspection and XRD analysis of the cross -sectioned samples showed no oxides scales demonstrating the removal of the residual oxygen inside the graphite enclosure and proper sealing by the aluminum wire and the Al-Ti melt.

4.1: X-Ray Diffraction

X-ray diffraction patterns for Zr-12 wt% Si samples and Zr -16 wt% Si samples heated at 1860 \degree C for 60, 120, 180, and 240 minutes are shown in figures 4.2 to 4.9. The analysis of the diffracting spectra identified $ZrB₂$ and ZrC in all four groups . A single phase silicide, ZrSi is shown to exist in both compositions of the samples processed at

1860 \degree C for all the four groups. In 120 minutes group, a Imost similar x-ray diffraction patterns were observed compared to samples annealed at 1860 \degree C for 60 minutes, with the exception of the appearance of another silicide, Zr_5Si_4 (tetragonal crystal structure). Almost identical patterns are acquired for samples allowed to react for 180 minutes and 240 minute s. One exception is the Zr -12 wt% Si sample reacted for 240 minutes, in which peaks matching silicide, Zr_2Si , was found (figure 4.8).

4.2: Microstructures

The SEM and optical micrograph for 60 minutes as shown in figure 4.10 and 4.11 points to the ZrB $_2$ precipitates (hexagonal crystal structure) and ZrC precipitates (face centered cubic crystal structure) dispersed in a Zr -Si melt. The unreacted B_4C is shown on the right in the optical micrograph. ZrB₂, ZrC and Zr $_{x}Si_{v}$ precipitates surrounded by the unreacted B_4C are shown in figure 4.11. B $_4C$ was observed in the samples reacted for 120 minutes too (figure 4.13), indicating incomplete reactions. But, micrographs for samples reacted for 180 and 240 minutes (figures 4.15 to 4.17) demonstrates complete reaction between B_4C and Zr-Si melt forming a continuous microstructure with ZrB $_2$, the most dominant phase.

4.3: Results Summary

 $ZrB₂$ was the main phase in the matrix after reaction. $ZrSi$ was the only silicide identified by XRD in all 4 groups. Zr $5Si_4$ was detected in 3 groups excluding the 60 minutes run. Zr $_2$ Si was spotted only in the Zr -16 wt% Si sample heated at the set temperature for 240 minutes. Other silicides like $Zr = 5Si_3$, Zr_3Si , and $ZrSi_2$ were not observed on the x -ray spectrum s. Micrographs for the 4 groups showed formation of ZrB_2 -ZrC composite in a solidified Zr-Si melt. Large amounts of free B_4C were observed

in the shorter runs of 60 minutes and 120 minutes and considerable porosity were observed in all the samples. To conclude, ZrB_2 and ZrC precipitates within a metal matrix of a Zr -Si alloy were successfully developed in both sets o f compositions heated at 1860° C for 60, 120, 180, and 240 minutes

Figure 4.1: Cross-section of a processed sample showing the effect of the levitation caused by the magnetic field of the induction furnace.

Figure 4.3: XRD diagram for Zr-16wt%Si held at 1860°C for 60 minutes. **Figure 4.3: XRD diagram for Zr-16wt%Si held at 1860°C for 60 minutes.**

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Figure 4.10: SEM Micrograph of ZrB2-ZrC precipitates surrounded by solidified Zr-Si melt and the unreacted B4C in sample held at 1860C for 60 minutes.

Figure 4.11: Micrograph of ZrB2-ZrC precipitates surrounded by solidified Zr-Si melt and the unreacted B4C in sample held at 1860C for 60 minutes.

Figure 4.12: Micrograph with a closer look at the unreacted B4C and ZrB2-ZrC-ZrxSiy precipitates in sample held at 1860C for 60 minutes.

Figure 4.13: Micrograph of ZrB2-ZrC-ZrxSiy precipitates encased within solidified Zr-Si melt in a sample held at 1860C for 120 minutes.

Figure 4.14: Micrograph with a closer look at the unreacted B4C and ZrB2-ZrC-ZrxSiy precipitates in sample held at 1860C for 120 minutes.

Figure 4.15: Micrograph of ZrB2-ZrC precipitates encased within solidified Zr-Si melt in a sample held at 1860C for 180 minutes.

Figure 4.16: Micrograph of ZrB2-ZrC precipitates in a completely reacted sample held at 1860C for 180 minutes.

held at 1860C for 240 minutes. held at 1860°C for 240 minutes.Figure 4.17: Micrograph with ZrB2-ZrC precipitates in a completely reacted sample

Chapter 5: DISCUSSION

5.1: Oxygen Potential Reduction within the graphite Enclosure

The absence of ZrO_2 and Al₂O₃ peaks in the x -ray diffraction patterns shown from figure 4.2 to figure 4.9, for the 2 different compositions of samples processed for 60 to 240 minutes indicate successful reduction of the oxygen potential within the graphite enclosure by the aluminum and t itanium slugs. The removal of oxygen can be explained with the help of the Ellingham diagram, which depicts Gibbs free energy of formation with temperature. The Ellingham diagram for the o xides (figure 5.1) indicates that at 2000 °C, Y_2O_3 is the most stable oxide, as demonstrated by the lowest free energy. For ZrO $_2$ and Al $_2O_3$, the lines intersect at 730°C, which suggests that at temperatures less than 730 \degree C, the liquid aluminum (melting temperature of 665 \degree C) has greater affinity for oxygen than zirconium does.

5.2: Phase Relations between Zr/B4C/Si

The Zr-B₄C-ZrSi₂ ternary phase diagram at 1900° C and 2400 $^{\circ}$ C shown in figures 5.2 and 5.3, respectively, suggests the formation of solid ZrB_2 and ZrC with liquid for the chosen stoichiometric ratios of Zr -12wt%Si (blue line) and Zr-16wt%Si (red line). The isothermal section of the phase diagram is observed at 2400 ^cC also, to account for the temperature rise inside the graphite crucible due to the highly exothermic nature of the reactions. Johnson et al. [6] reported adiabatic reaction temperatures to reach around 2300 \degree C-2400 \degree C during the processing of ZrB $_{2}$ -ZrC-Zr composites. Three zirconium silicides, ZrSi, Zr₂Si and Zr₅Si₃ are observed in the phase

diagrams. The compound SiB $_{14}$, formed by the reaction between B $_{4}$ C and SiB $_{6}$, decomposes before 2400° C is reached and was never observed on the XRD patterns.

5.3: X-Ray Diffraction

 The XRD spectrums (figures 4.2 to 4.9) for the samples reacted for 60. 120, 180, and 240 minutes, indicates the formation of ZrB $_2$ and ZrC precipitates in a solidified Zr -Si melt. ZrSi, is the only silicide to make an appearance in XRD spectrums for all the samples. This suggests the ZrSi prevails over all other silicides to become the main silicide. There was no considerable difference observed in the phases detected for the 2 different stoichiometric ratios due its closeness on the Zr -Si phase diagram [6]. The formation of ZrSi means the reaction moved to the left of Zr_{3} Si on the Zr -Si phase diagram shown in figure 2.1. To understand the formation of $Zr_{5}Si_{4}$ in all the samples except for samples reacted for 60 minutes, Ellingham diagrams for silicides are plotted. The Gibbs free energy of f ormation for the different silicides was generated using FactSage. Table 5.1 shows the Gibbs free energy of formation at temperatures, 200 \degree C, 800 \degree C, 1500 \degree C, 2000 \degree C, and 2500 \degree C. In the plot of \triangle G vs. temperature (fig ure 5.4), Zr_5Si_4 is the most stable silicide, which explains its presence in the XRD results. Zr $_5Si_3$ is the second most stable silicide, which is a discrepancy due its metastable nature at temperatures lower than 1745° C, which is not available on the FactSage database. The formation of Zr_2Si in the $Zr-16wt\%Si$ sample reacted for 240 minutes is probably due to separate magnetic field mixing or kinetic problem with the reaction not proceeding to form Zr-Si or Zr_5Si_4

5.4: Microstructures

 The microstructure images for the samples reacted for 60, 120, 180, and 240 minutes are shown from figures 4.10 to 4.17. The microstructures obtained are as suggested by the phase diagram with ZrB_2 and ZrC precipitates dispersed in solidified liquid. There was considerable unreacted $B \sim 4C$ in the 60 minutes and 120 minutes samples. This is a result of insufficient time for the reactants to achieve thermo chemical equilibria as a more continuous microstructures with little unreacted B $_4C$ were observed in the 180 minutes and 240 minutes samples. The formation of ZrB_2 and ZrC surrounded by solidified Zr-Si melt is due to the melting of zirconium slugs to form Zr -Si melt which reacts with B $_{4}$ C to form ZrB $_{2}$ and ZrC. On a Zr -B-C ternary, the join representing the Zr liquid reacting with B $_4C$ is show n in figure 2.4. Through the mass balance, the ZrC and ZrB $_2$ are formed as necessitated by the diffusional path crossing the join at least once, The shaded areas on either side of the join must be equal. Zr_5Si_3 appears in the Zr-B4C-Si ternary phase diagram but is not seen in the samples due to its metastable state at lower temperatures [Okamoto-1990].

Figure 5.1: Ellingham Diagram for oxides.

Figure 5.3: Zr-B4C-Si Pseudo-Ternary Phase Diagram at 2400C.

Table 5.1 Gibbs free energy of formation for zirconium silicides.

Temperature $^{\circ}C$	Zr_3Si kJ/mol	Zr ₂ Si kJ/mol	Zr_3Si_2 kJ/mol	Zr_5Si4 kJ/mol	ZrSi kJ/mol	ZrSi ₂ kJ/mol
200	-231	-223	$-422.$	-763	-163	-168
800	-214	-210	-395	-721	-155	-163
1500	-188	-199	-351	-648	-145	-149
2000	-156	-175	-289	-534	-124	-111

Figure 5.4: Ellingham Diagram for Zirconium Silicides.

Chapter 6: CONCLUSION

 Two compositions of stoichiometric ratios, Zr-12wt%Si and Zr-16wt%Si, were reacted with B₄C at 1860 °C f or 60 minutes, 120, 180, and 240 to determine the relationship between time and reactivity. The processed samples were characterized using an optical microscope and x-ray diffraction (XRD). Microstructures with ZrB_2 and ZrC precipitates surrounded by solidified Zr-Si melt were observed in all the samples as expected with ZrSi, the main phase of silicide detected. Free B_4C was detected in the 60 minutes and 120 minutes due to short durat ion of reaction time. One concern was the considerable porosity observed due to the furnace's electromagnetic field, which levitated the Zr liquid, but the ZrO $_{2}$ -Y₂O₃ crucible shield decreased the levitation significantly. The Zr-Si liquid reacted completely with B $_4C$ as observed in the 180 minutes and 240 minutes samples suggesting sufficient time for the reactants to attain phase equilibria was reached for the ultrahigh temperatures achieved.

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